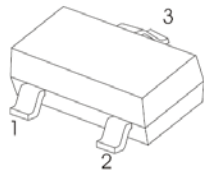
Features

- $V_{DS\ (V)}$ = 30V
- $R_{DS(ON)}$ < 250mΩ (V_{GS} = 10V)
- $R_{DS(ON)}$ < 400mΩ (V_{GS} = 4.5V)

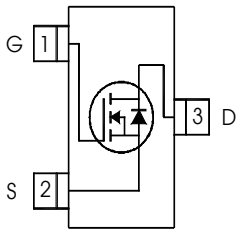
SOT－23



1. GATE
2. SOURCE
3. DRAIN

Description

- Generation VTechnology UltraLowOn-Resistance
- Low Profile (<1.1mm)
- Available in Tape and Reel
- Fast Switching
- Lead-Free
- RoHS CompliantHalogen-Free



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	1.2	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V	0.93	
I_{DM}	Pulsed Drain Current ①	7.3	
P_D @T_A = 25°C	Power Dissipation	540	mW
	Linear Derating Factor	4.3	mW/°C
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy⑤	3.9	mJ
dv/dt	Peak diode Recovery dv/dt②	5.0	V/ns
T_J ,T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

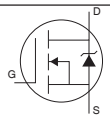
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ④	——	230	°C/W

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	–––	–––	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.029	–––	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	–––	250	mΩ	V_{GS} = 10V, I_D = 0.91A ③
		–––	–––	400		V_{GS} = 4.5V, I_D = 0.46A ③
$V_{GS(th)}$	Gate Threshold Voltage	1.0	–––	–––	V	V_{DS} = V_{GS}, I_D = 250μA
g_{fs}	Forward Transconductance	0.87	–––	–––	S	V_{DS} = 10V, I_D = 0.46A
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	1.0	μA	V_{DS} = 24V, V_{GS} = 0V
		–––	–––	25		V_{DS} = 24V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	-100	nA	V_{GS} = -20V
	Gate-to-Source Reverse Leakage	–––	–––	100		V_{GS} = 20V
Q_g	Total Gate Charge	–––	3.3	5.0	nC	I_D = 0.91A
Q_{gs}	Gate-to-Source Charge	–––	0.48	0.72		V_{DS} = 24V
Q_{gd}	Gate-to-Drain ("Miller") Charge	–––	1.1	1.7		V_{GS} = 10V, See Fig. 6 and 9 ③
$t_{d(on)}$	Turn-On Delay Time	–––	3.9	–––	ns	V_{DD} = 15V
t_r	Rise Time	–––	4.0	–––		I_D = 0.91A
$t_{d(off)}$	Turn-Off Delay Time	–––	9.0	–––		R_G = 6.2Ω
t_f	Fall Time	–––	1.7	–––		R_D = 16Ω, See Fig. 10 ③
C_{iss}	Input Capacitance	–––	85	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	34	–––		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	–––	15	–––		f = 1.0MHz, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	0.54	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	7.3		
V_{SD}	Diode Forward Voltage	–––	–––	1.2	V	T_J = 25°C, I_S = 0.91A, V_{GS} = 0V ③
t_{rr}	Reverse Recovery Time	–––	26	40	ns	T_J = 25°C, I_F = 0.91A
Q_{rr}	Reverse RecoveryCharge	–––	22	32	nC	di/dt = 100A/μs ③

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② I_{SD} ≤ 0.91A, di/dt ≤ 120A/μs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 150°C

③ Pulse width ≤ 300μs; duty cycle ≤ 2%.

④ Surface mounted on FR-4 board, t ≤ 5sec.

⑤ Limited by T_{Jmax}, starting T_J = 25°C, L = 9.4mH, R_G = 25Ω, I_{AS} = 0.9A.

Typical Electrical Characteristics

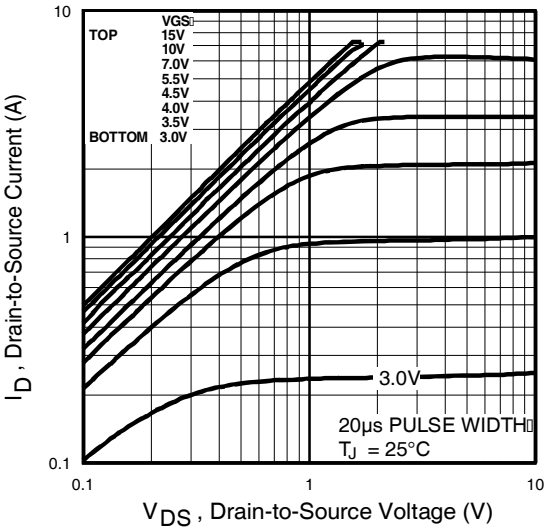


Fig 1. Typical Output Characteristics

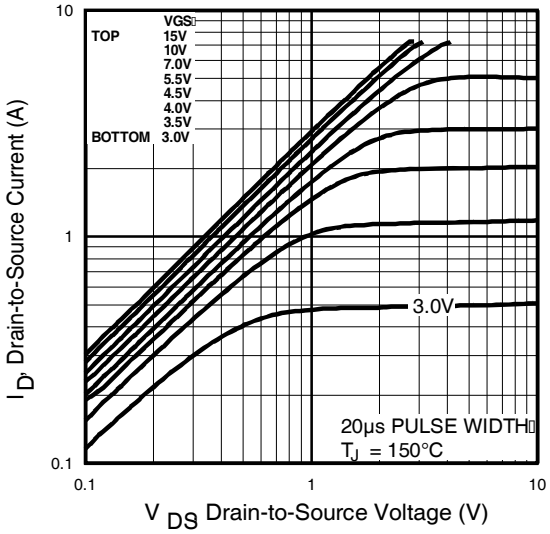


Fig 2. Typical Output Characteristics

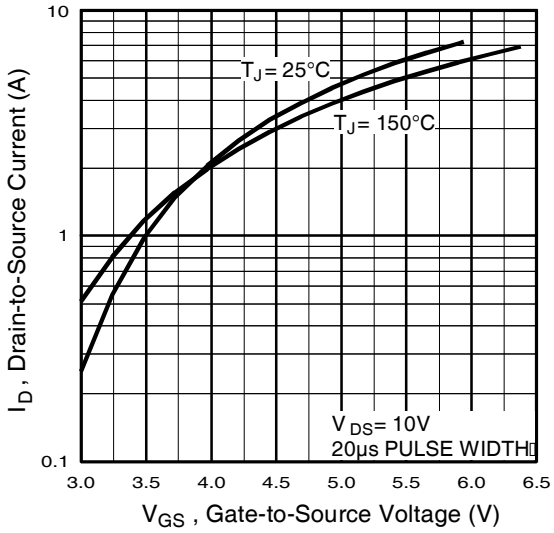


Fig 3. Typical Transfer Characteristics

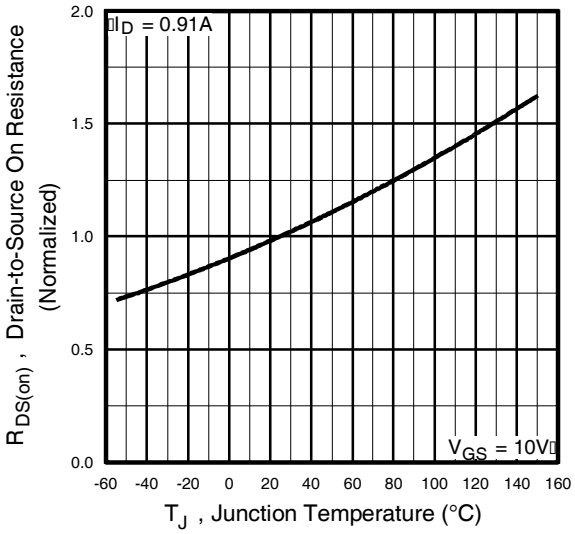


Fig 4. Normalized On-Resistance Vs. Temperature

Typical Electrical Characteristics

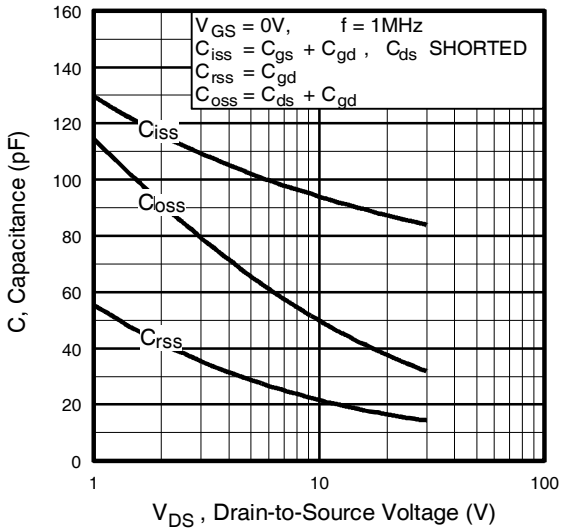


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

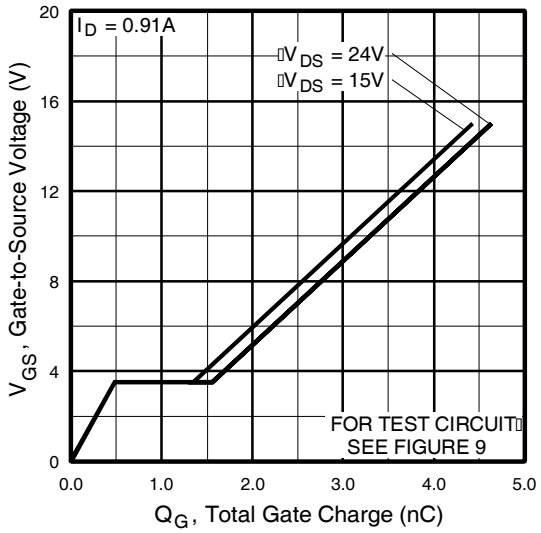


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

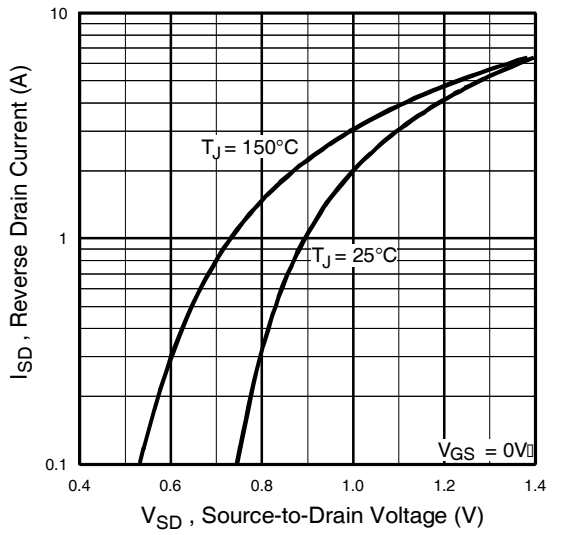


Fig 7. Typical Source-Drain Diode Forward Voltage

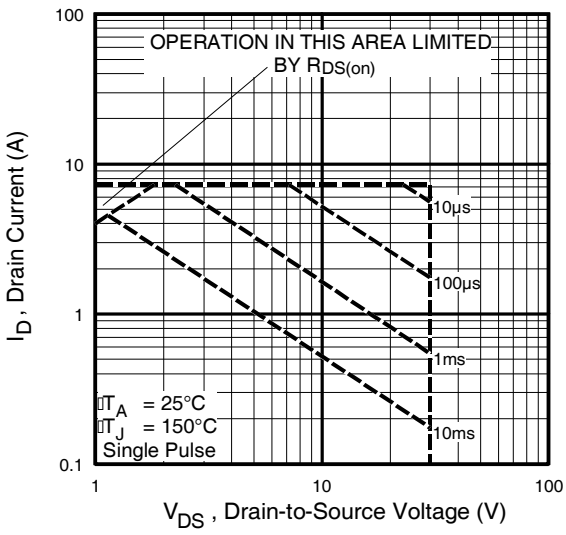


Fig 8. Maximum Safe Operating Area

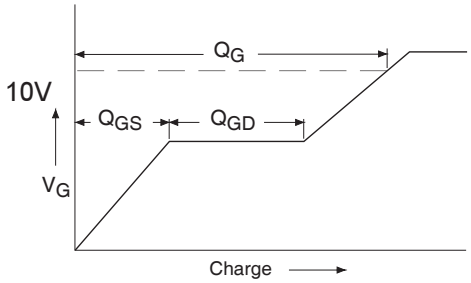


Fig 9a. Basic Gate Charge Waveform

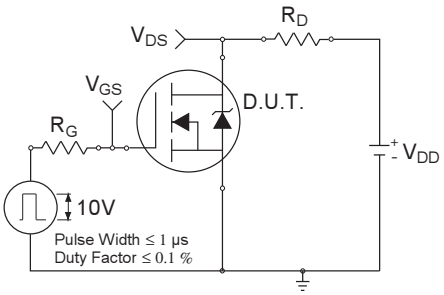


Fig 10a. Switching Time Test Circuit

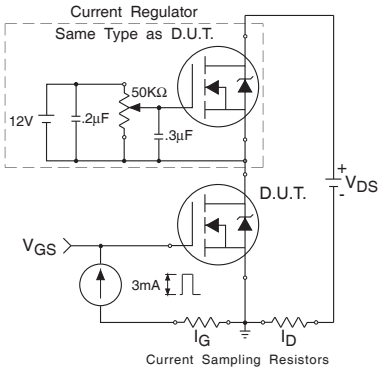


Fig 9b. Gate Charge Test Circuit

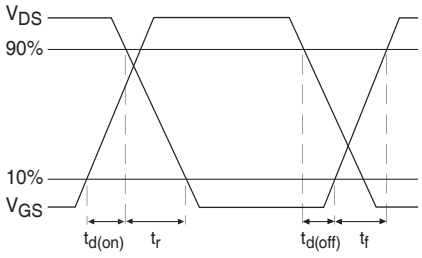


Fig 10b. Switching Time Waveforms

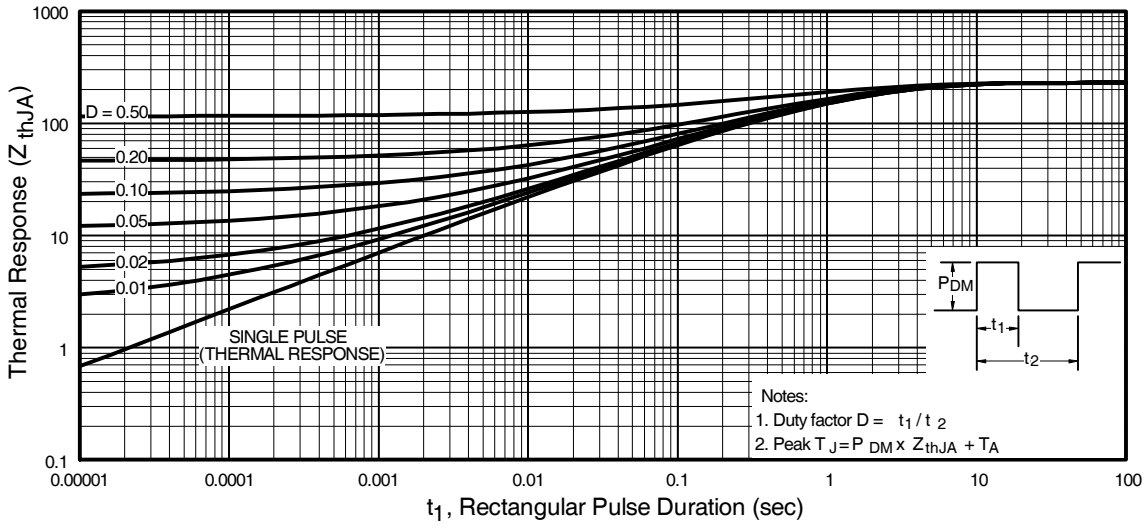


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

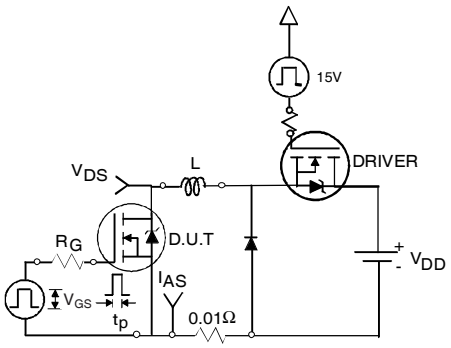


Fig 12a. Unclamped Inductive Test Circuit

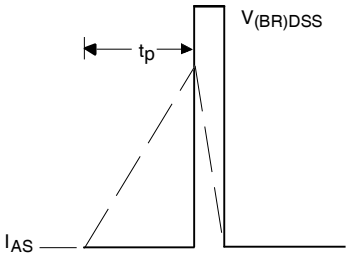


Fig 12b. Unclamped Inductive Waveforms

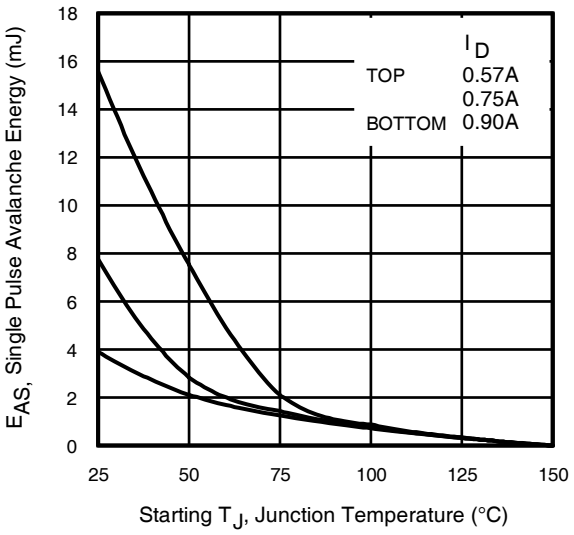


Fig 12c. Maximum Avalanche Energy vs. Drain Current

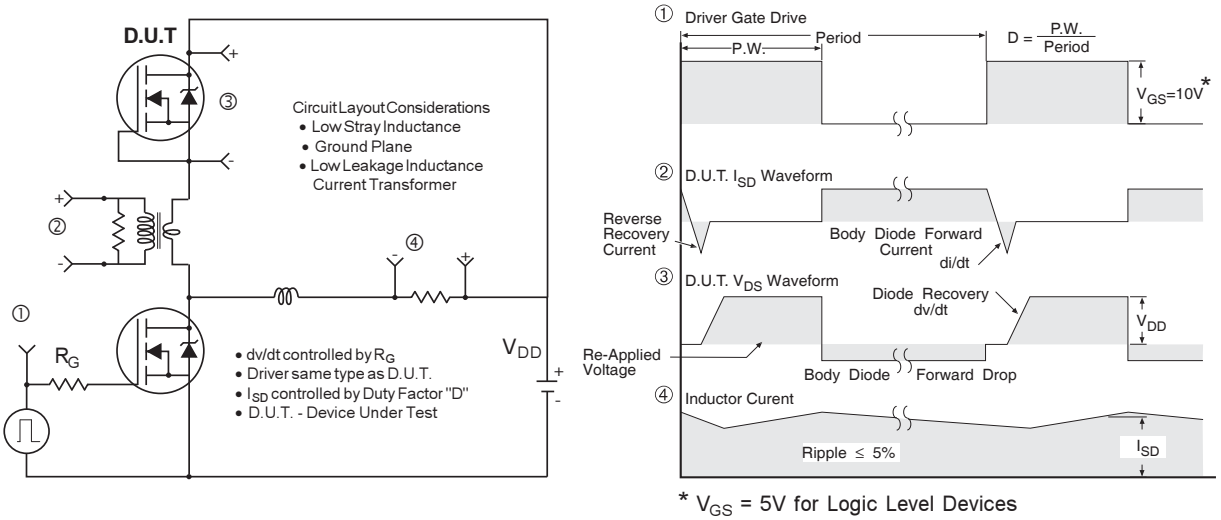
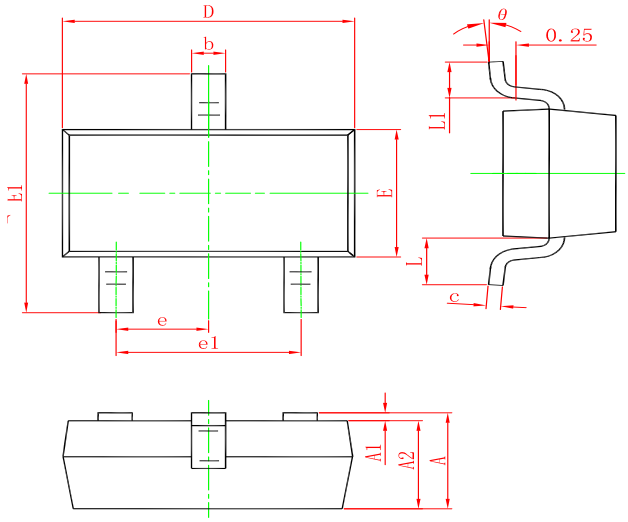


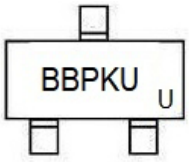
Fig 13. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
UMW IRLML2803TR	SOT-23	3000	Tape and reel

单击下面可查看定价，库存，交付和生命周期等信息

>>UMW(友台半导体)